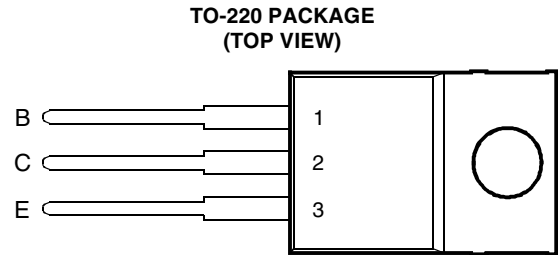


- 80 W at 25°C Case Temperature
- 7 A Continuous Collector Current
- 10 A Peak Collector Current
- Maximum  $V_{CE(sat)}$  of 2 V at  $I_C = 5 A$
- $I_{CEX(sus)}$  7 A at rated  $V_{(BR)CEO}$



Pin 2 is in electrical contact with the mounting base.

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**absolute maximum ratings at 25°C case temperature (unless otherwise noted)**

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ( $I_E = 0$ )	TIP150	$V_{CBO}$	300	V
	TIP151		350	
	TIP152		400	
Collector-emitter voltage ( $I_B = 0$ )	TIP150	$V_{CEO}$	300	V
	TIP151		350	
	TIP152		400	
Emitter-base voltage		$V_{EBO}$	8	V
Continuous collector current		$I_C$	7	A
Peak collector current (see Note 1)		$I_{CM}$	10	A
Continuous base current		$I_B$	1.5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		$P_{tot}$	80	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		$P_{tot}$	2	W
Operating junction temperature range		$T_j$	-65 to +150	°C
Storage temperature range		$T_{stg}$	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		$T_L$	260	°C

- NOTES: 1. This value applies for  $t_p \leq 5$  ms, duty cycle  $\leq 10\%$ .  
 2. Derate linearly to 150°C case temperature at the rate of 0.64 W/°C.  
 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

**PRODUCT INFORMATION**

**electrical characteristics at 25°C case temperature**

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CBO}$ Collector-base breakdown voltage	$I_C = 1 \text{ mA}$	$I_E = 0$	TIP150 TIP151 TIP152	300 350 400			V
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 10 \text{ mA}$ (see Note 4)	$I_B = 0$	TIP150 TIP151 TIP152	300 350 400			V
$I_{CEO}$ Collector-emitter cut-off current	$V_{CE} = 300 \text{ V}$ $V_{CE} = 350 \text{ V}$ $V_{CE} = 400 \text{ V}$	$I_B = 0$ $I_B = 0$ $I_B = 0$	TIP150 TIP151 TIP152			250 250 250	$\mu\text{A}$
$I_{CEX(sus)}$ Collector-emitter sustaining current	$V_{CLAMP} = V_{(BR)CEO}$			7			A
$I_{EBO}$ Emitter cut-off current	$V_{EB} = 8 \text{ V}$	$I_C = 0$				15	mA
$h_{FE}$ Forward current transfer ratio	$V_{CE} = 5 \text{ V}$ $V_{CE} = 5 \text{ V}$ $V_{CE} = 5 \text{ V}$	$I_C = 2.5 \text{ A}$ $I_C = 5 \text{ A}$ $I_C = 7 \text{ A}$	(see Notes 4 and 5)	150 50 15			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 10 \text{ mA}$ $I_B = 100 \text{ mA}$ $I_B = 250 \text{ mA}$	$I_C = 1 \text{ A}$ $I_C = 2 \text{ A}$ $I_C = 5 \text{ A}$	(see Notes 4 and 5)			1.5 1.5 2	V
$V_{BE(sat)}$ Base-emitter saturation voltage	$I_B = 100 \text{ mA}$ $I_B = 250 \text{ mA}$	$I_C = 2 \text{ A}$ $I_C = 5 \text{ A}$	(see Notes 4 and 5)			2.2 2.3	V
$V_{EC}$ Parallel diode forward voltage	$I_E = 7 \text{ A}$	$I_B = 0$	(see Notes 4 and 5)			3.5	V
$h_{fe}$ Small signal forward current transfer ratio	$V_{CE} = 5 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ kHz}$	200			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = 5 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ MHz}$	10			
$C_{ob}$ Output capacitance	$V_{CB} = 10 \text{ V}$	$I_E = 0$	$f = 1 \text{ MHz}$			100	pF

NOTES: 4. These parameters must be measured using pulse techniques,  $t_p = 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

**thermal characteristics**

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.56	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	$^{\circ}\text{C}/\text{W}$
$C_{\theta C}$ Thermal capacitance of case		0.9		$\text{J}/^{\circ}\text{C}$

**inductive-load-switching characteristics at 25°C case temperature**

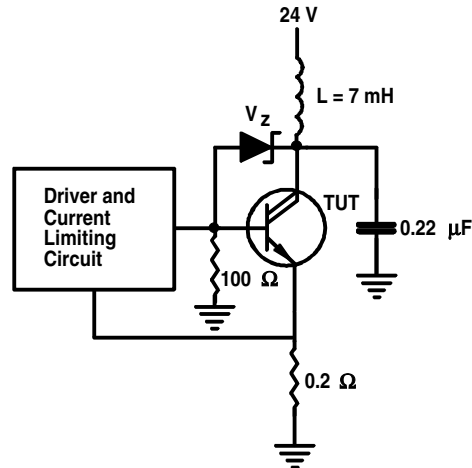
PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
$t_{sv}$ Voltage storage time	$I_C = 5 \text{ A}$ $V_{(clamp)} = V_{(BR)CEO}$	$I_{B(on)} = 250 \text{ mA}$	$R_{BE} = 47 \Omega$		3.9		$\mu\text{s}$
$t_{si}$ Current storage time					4.7		$\mu\text{s}$
$t_{rv}$ Voltage transition time					1.2		$\mu\text{s}$
$t_{ti}$ Current transition time					1.2		$\mu\text{s}$
$t_{xo}$ Cross-over time					2.0		$\mu\text{s}$

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

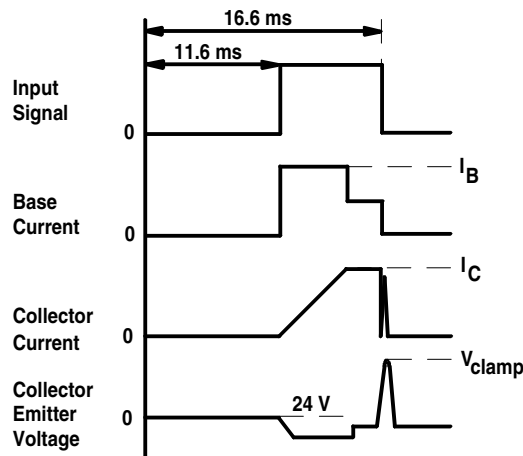
**PRODUCT INFORMATION**

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Specifications are subject to change without notice.

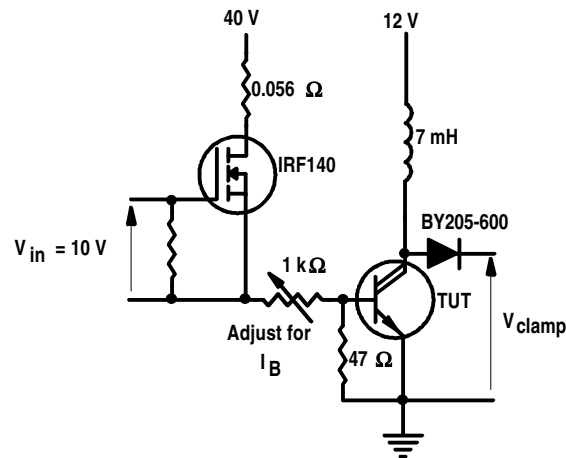
**PARAMETER MEASUREMENT INFORMATION**



**Figure 1. Functional Test Circuit**



**Figure 2. Functional Test Waveforms**



**Figure 3. Switching Test Circuit**

**PRODUCT INFORMATION**

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**TYPICAL CHARACTERISTICS**

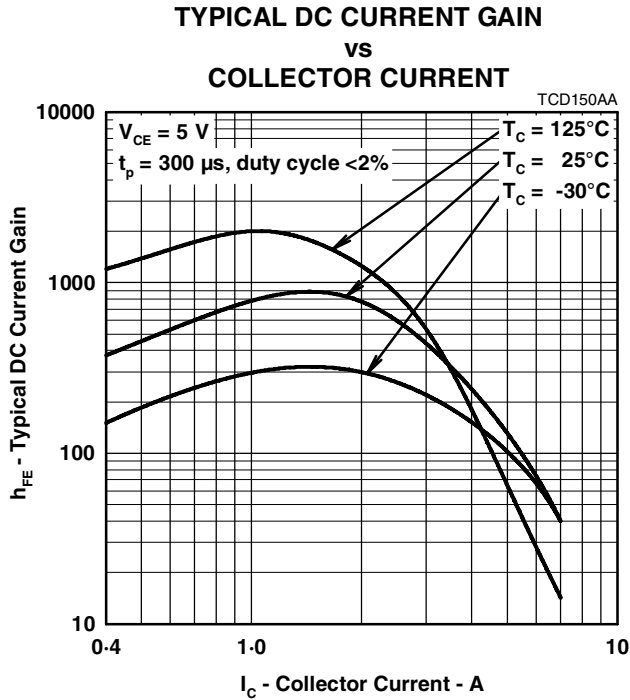


Figure 4.

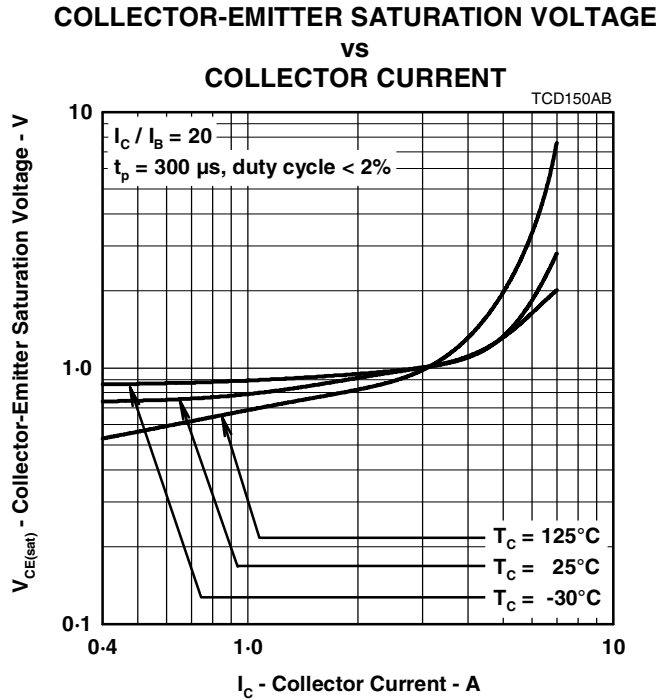


Figure 5.

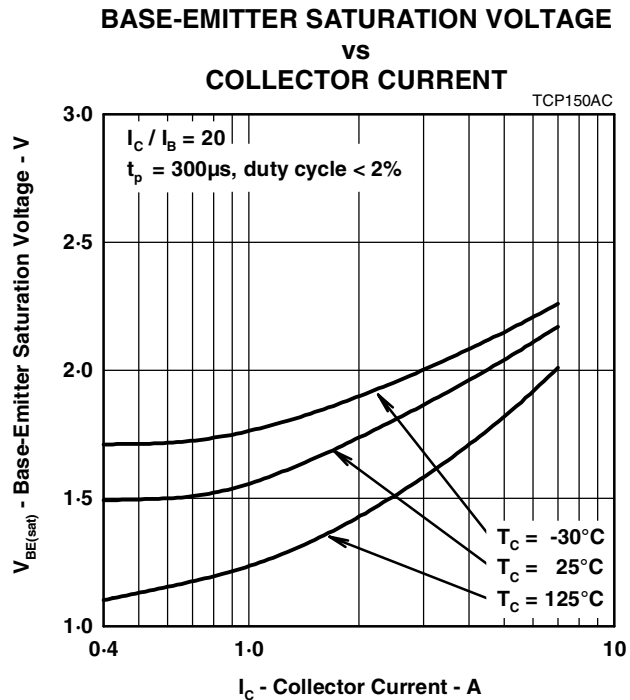


Figure 6.

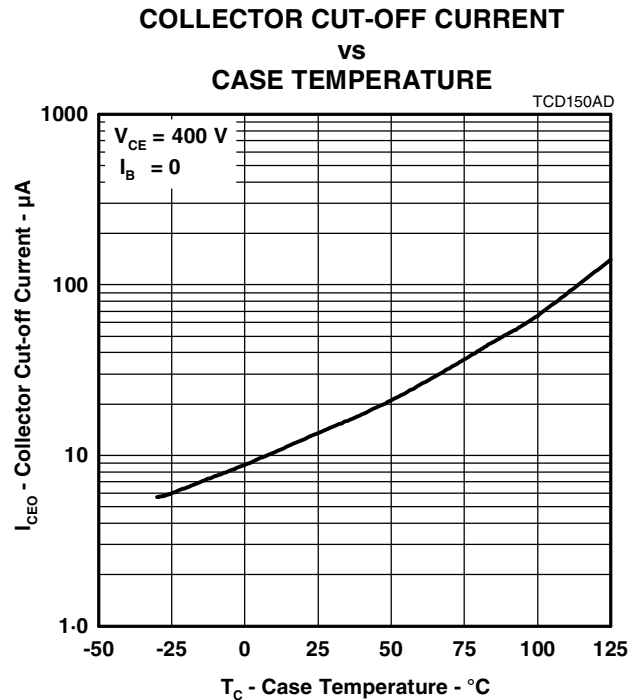


Figure 7.

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**MAXIMUM SAFE OPERATING REGIONS**

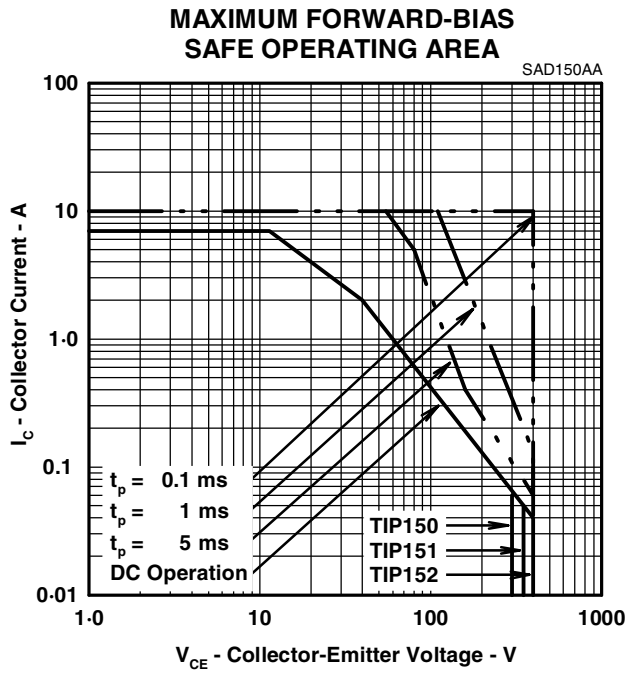


Figure 8.

**THERMAL INFORMATION**

**MAXIMUM POWER DISSIPATION  
vs  
CASE TEMPERATURE**

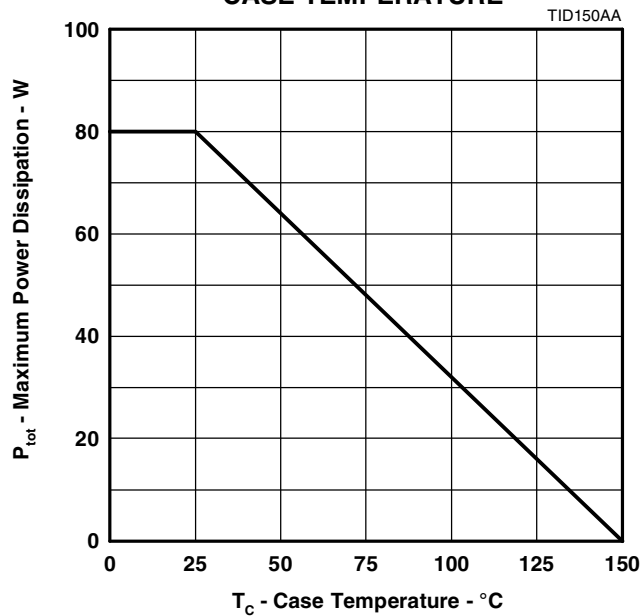


Figure 9.

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